SPECIFICATION

DEVICE NAME : Power MOSFET

TYPE NAME : 2SK2918-01

SPEC. No. :

Fuji Electric Co., Ltd.
Matsumoto Factory

	DATE	NAME	APPROVED
DRAWN			
CHECKED			

Fuji Electric Co.,Ltd.

DWG.NO.

H04-004-07

1. Scope
This specifies Fuji power MOSFET 2SK2918-01

2. Construction N-channel enhancement mode power MOSFET

3. Application for switching

4. Outview TO-220 Outview See to 5/11 page

5. Absolute maximum ratings at Tc=25℃ (unless otherwise specified)

Description	Symbol	Characteristics	Unit	
Drain-source voltage	V_{DS}	200	V	
Drain-gate voltage	V_{DGR}	200	V	
Continuous Drain current	I_D	± 20	A	
Pulsed drain current	I_{Dpulse}	± 80	A	
Gate-source voltage	V_{GS}	± 30	V	
Maximum power dissipation	P_D	80	W	
Operating and storage temperature range	T_{ch}	150	℃	
	T_{stg}	-55 ~ +150	℃	

6. Electrical characteristics at Tc=25℃ (unless otherwise specified)
Static ratings

Description	Symbol	Conditions		Characteristics			Unit
				Min.	Typ.	Max.	
Drain-source breakdown voltage	BV_{DSS}	I_D =1mA V_{GS}=0V		200			V
Gate threshold voltage	$V_{GS(th)}$	I_D =1mA V_{DS}=V_{GS}		2.5	3.0	3.5	V
Zero gate voltage drain current	I_{DSS}	V_{DS}=200V V_{GS}= 0V	T_{ch}= 25℃		10	500	μA
	I_{DSS}		T_{ch}=125℃		0.2	1.0	mA
Gate-source leakage current	I_{GSS}	V_{GS}=±30V V_{DS}= 0V			10	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	I_D =10A V_{GS}=10V			100	130	mΩ

Dynamic ratings

Description	Symbol	Conditions	Characteristics			Unit
			Min.	Typ.	Max.	
Forward transconductance	gfs	I_D = 10A V_{DS}= 25V	7.0	15.0		S
Input capacitance	Ciss	V_{DS}=25V V_{GS}= 0V f =1MHz		1800	2700	pF
Output capacitance	Coss			320	480	pF
Reverse transfer capacitance	Crss			80	120	pF
Turn-on time	td(on)	V_{CC}=150V V_{GS}= 10V I_D = 20A R_{GS}= 10Ω		15	25	ns
	tr			60	90	ns
Turn-off time	td(off)			65	100	ns
	tf			60	90	ns

Reverse diode

Description	Symbol	Conditions	Characteristics			Unit
			Min.	Typ.	Max.	
Avalanche capability	I_{AV}	L=100μH, T_{ch}=25℃ *See Fig.1 and 2	20.0			A
Diode forward on-voltage	V_{SD}	I_F = 2 × I_{DR} V_{GS}=0V, T_{ch}=25℃		1.06	1.59	V
Reverse recovery time	t_{rr}	I_F = I_{DR} V_{GS}=0V $-dI_F/dt$=100A/μs T_{ch}=25℃		145		ns
Reverse recovery charge	Q_{rr}			900		μC

7. Thermal resistance

Description	Symbol	Conditions	Characteristics			Unit
			Min.	Typ.	Max.	
Thermal resistance	Rth_{ch}-c				1.56	℃/W
	Rth_{ch}-a				75.0	℃/W

Fig. 1 Test circuit

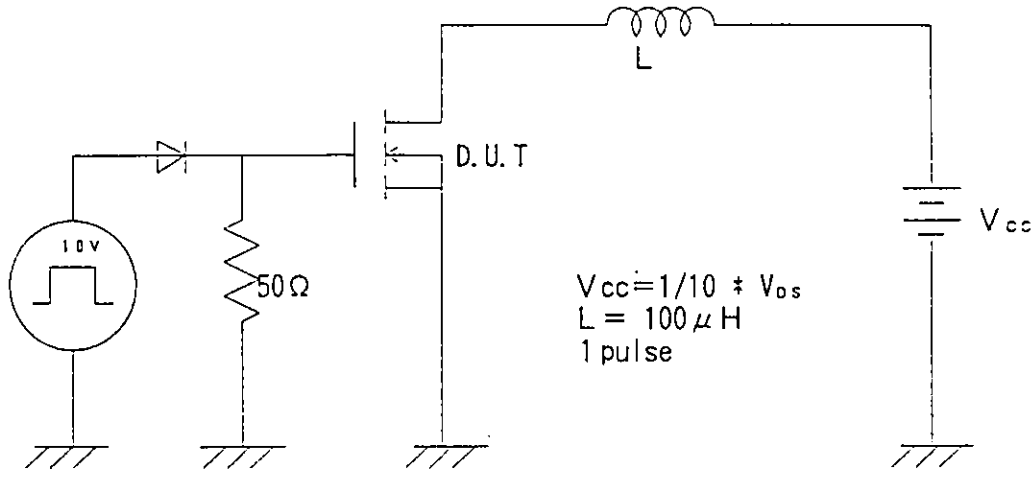
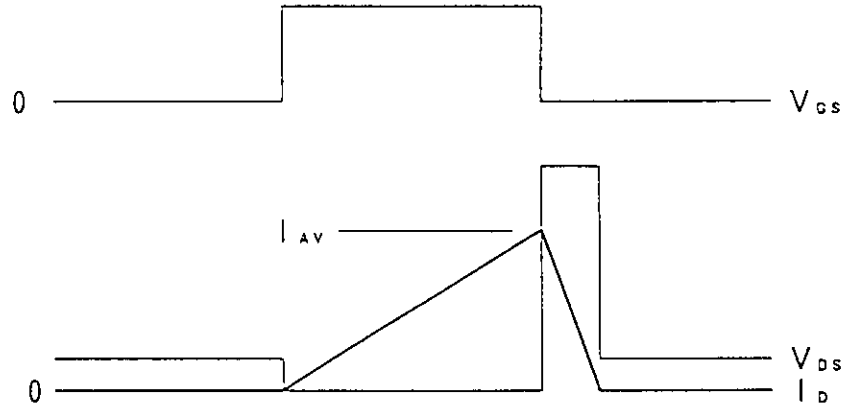
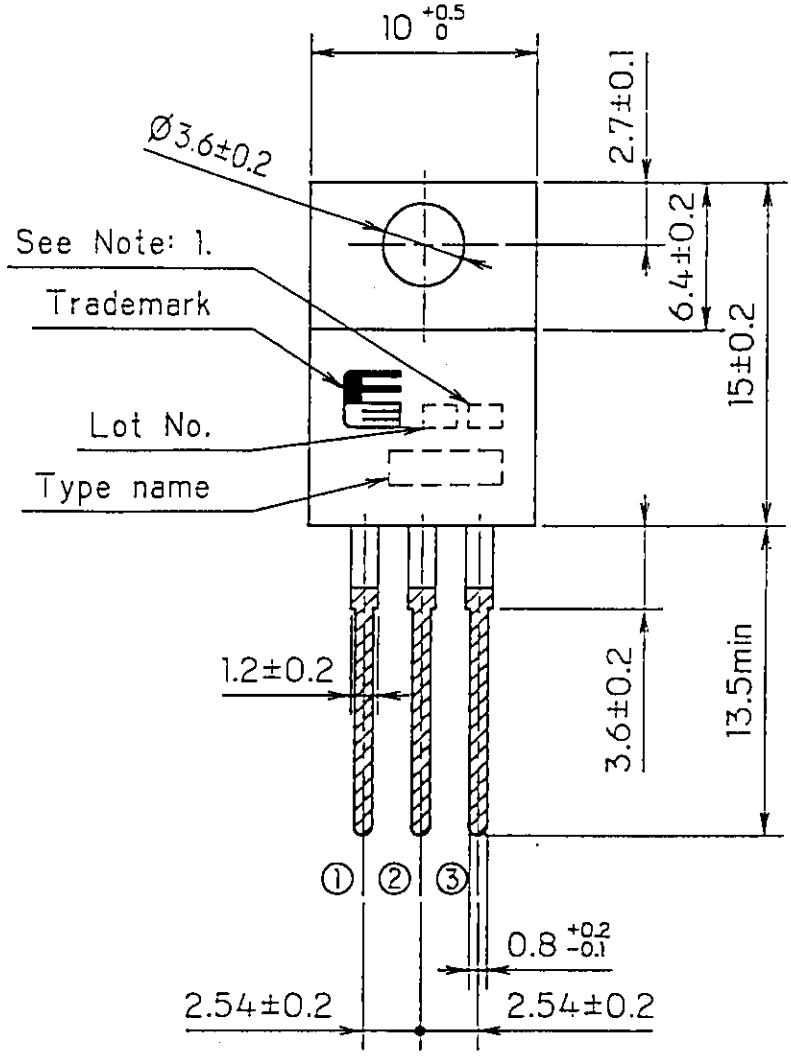


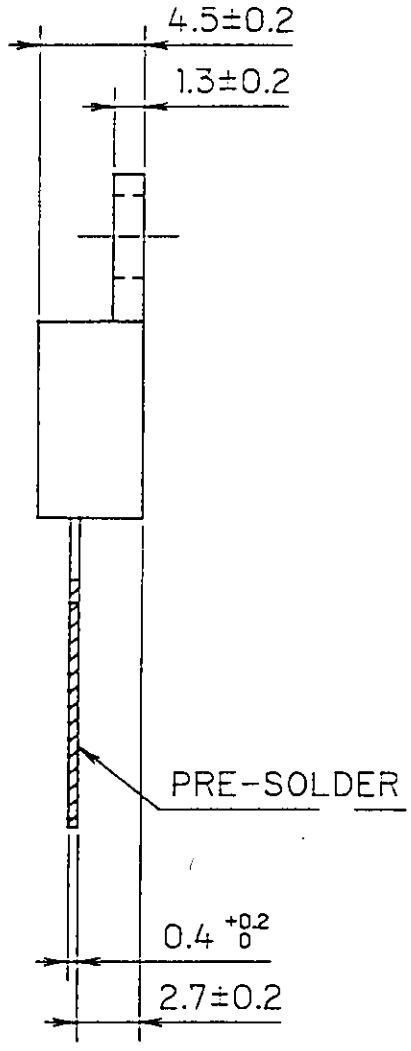
Fig. 2 Operating waveforms

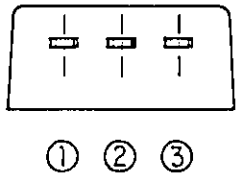


FUJI POWER MOS FET

TYPE : 2SK2918-01







CONNECTION

① GATE
② DRAIN
③ SOURCE

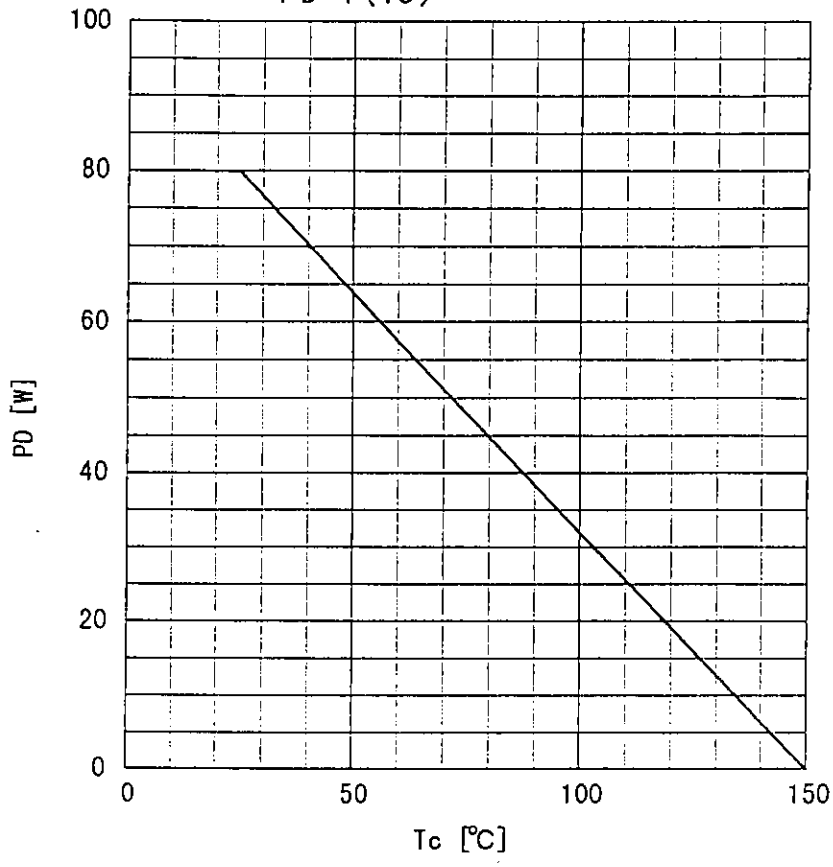
JEDEC : TO-220AB

Note: 1. $V_{GS(th)}$ selected code.

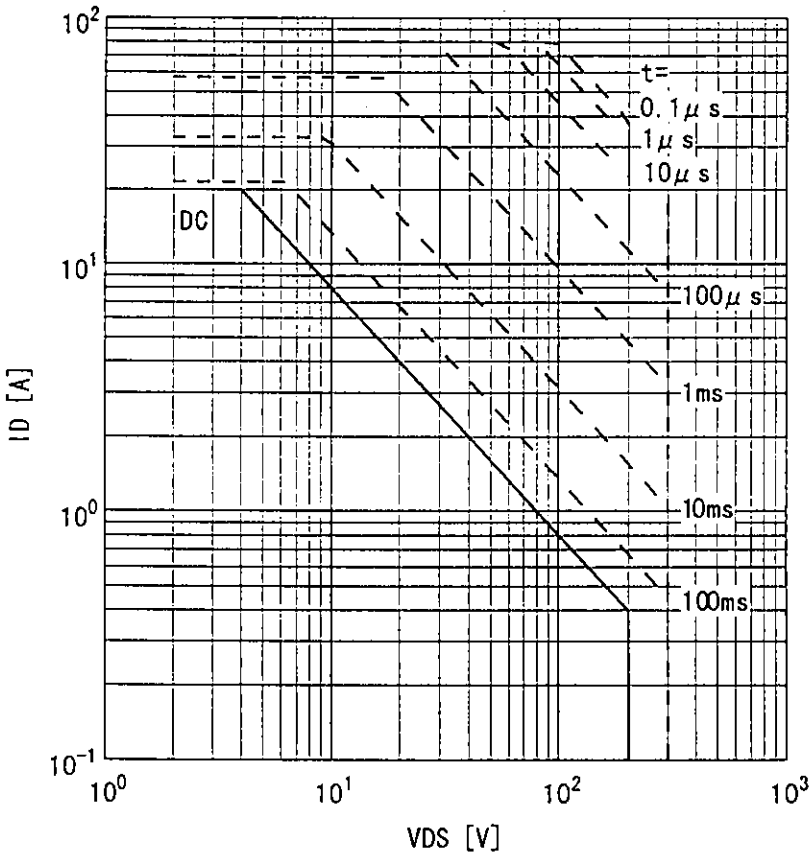
Note: 1. Guaranteed mark of avalanche ruggedness.

DIMENSIONS ARE IN MILLIMETERS.

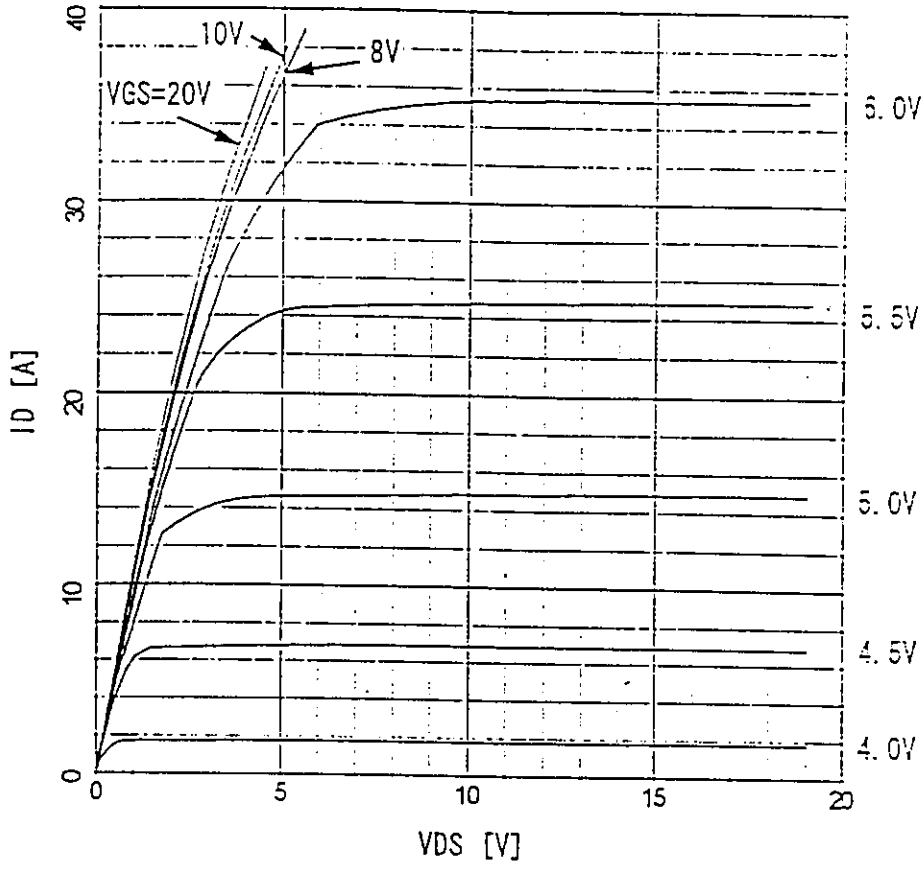
Power Dissipation
PD=f(Tc)



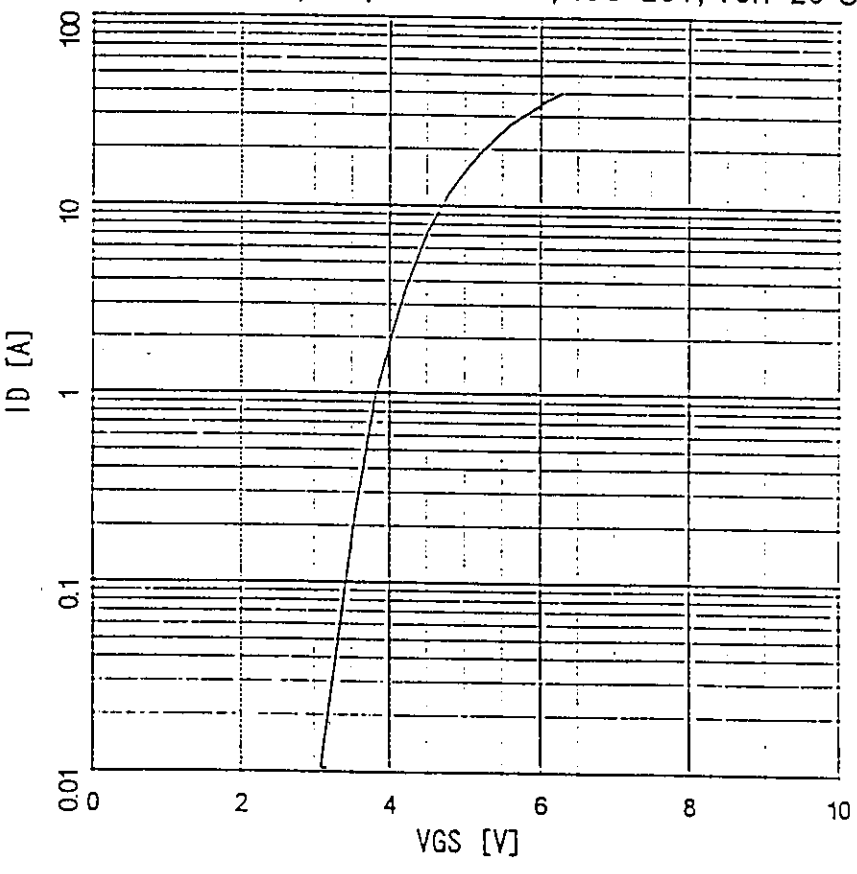
Safe operating area
ID=f(VDS) : D=0.01, Tc=25°C



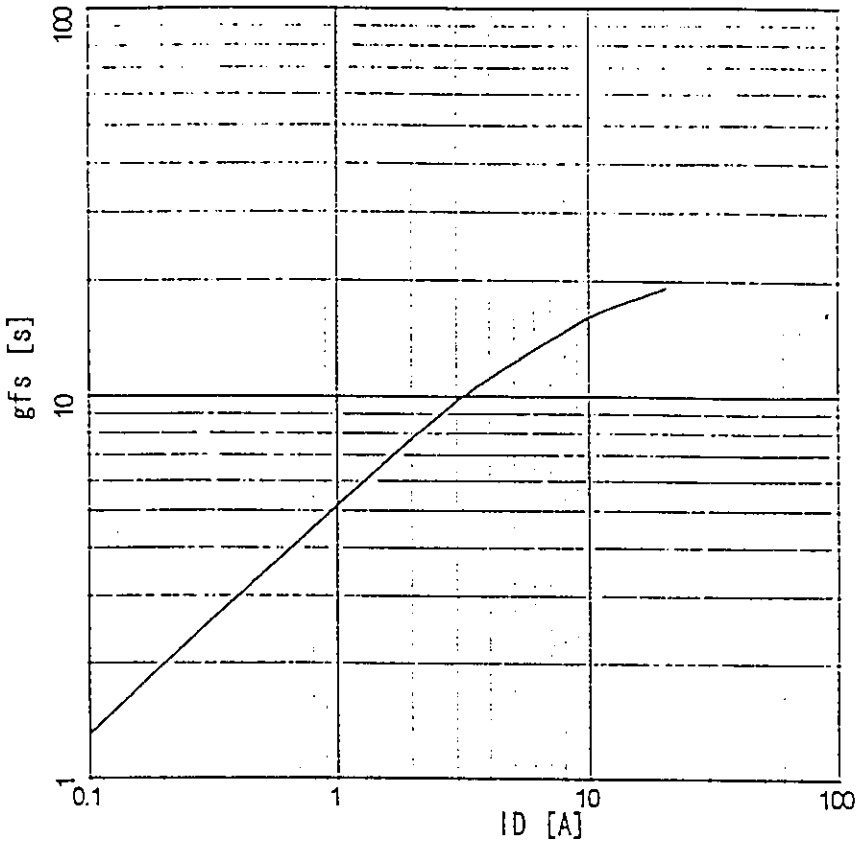
Typical output characteristics
ID=f(VDS):80μs pulse test, Tch=25°C



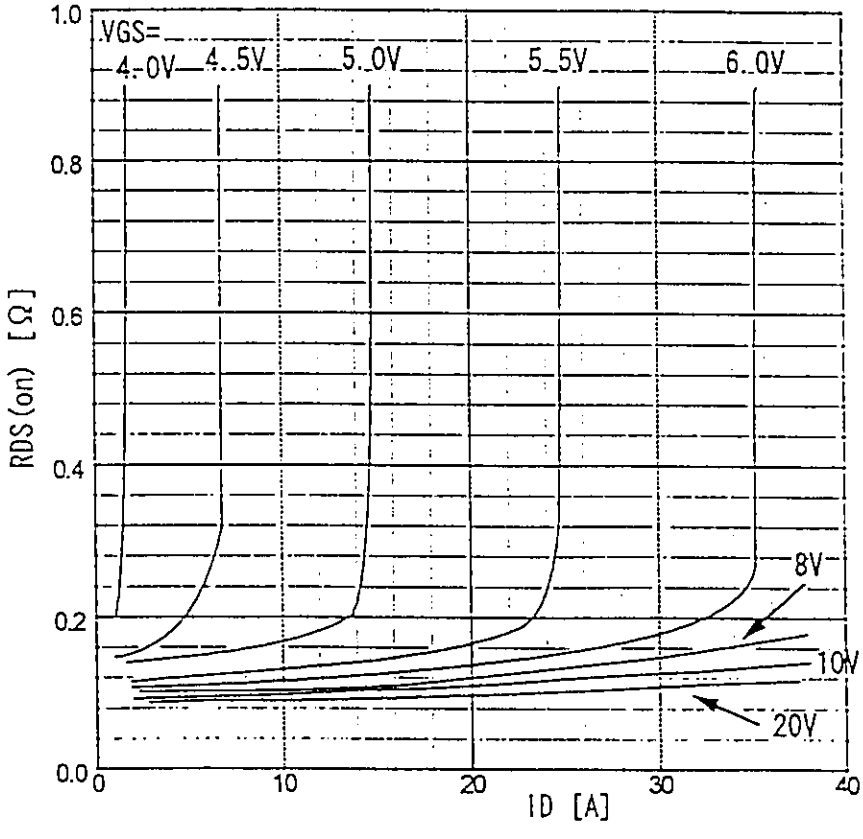
Typical transfer characteristic
ID=f(VGS):80μs pulse test, VDS=25V, Tch=25°C



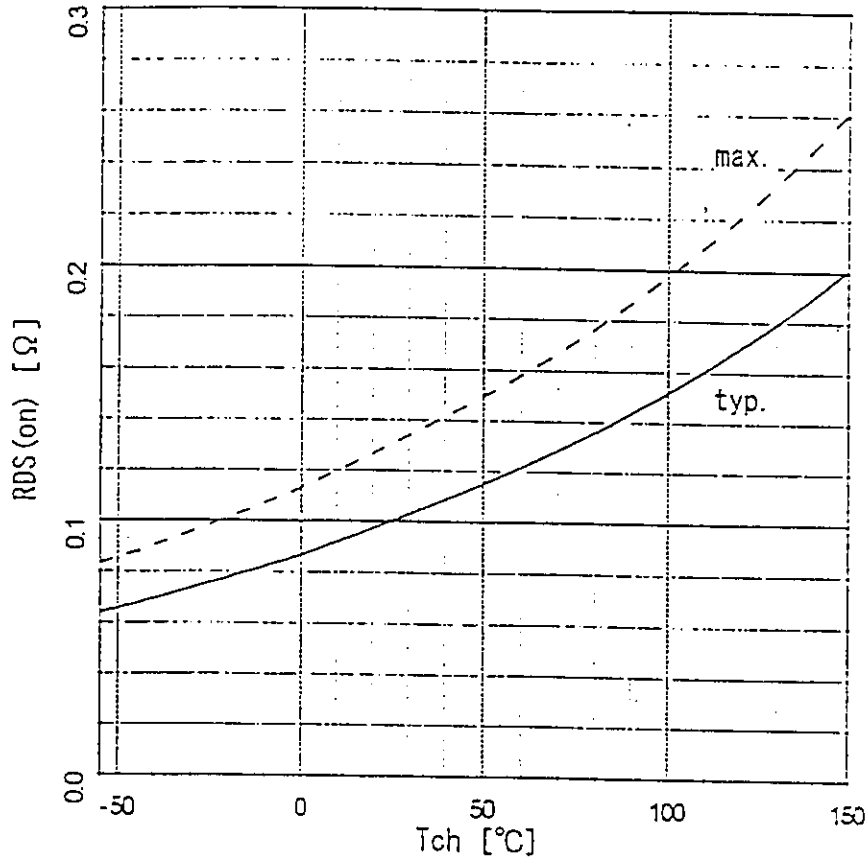
Typical transconductance
gfs=f(ID):80μs pulse test, VDS=25V, Tch=25℃



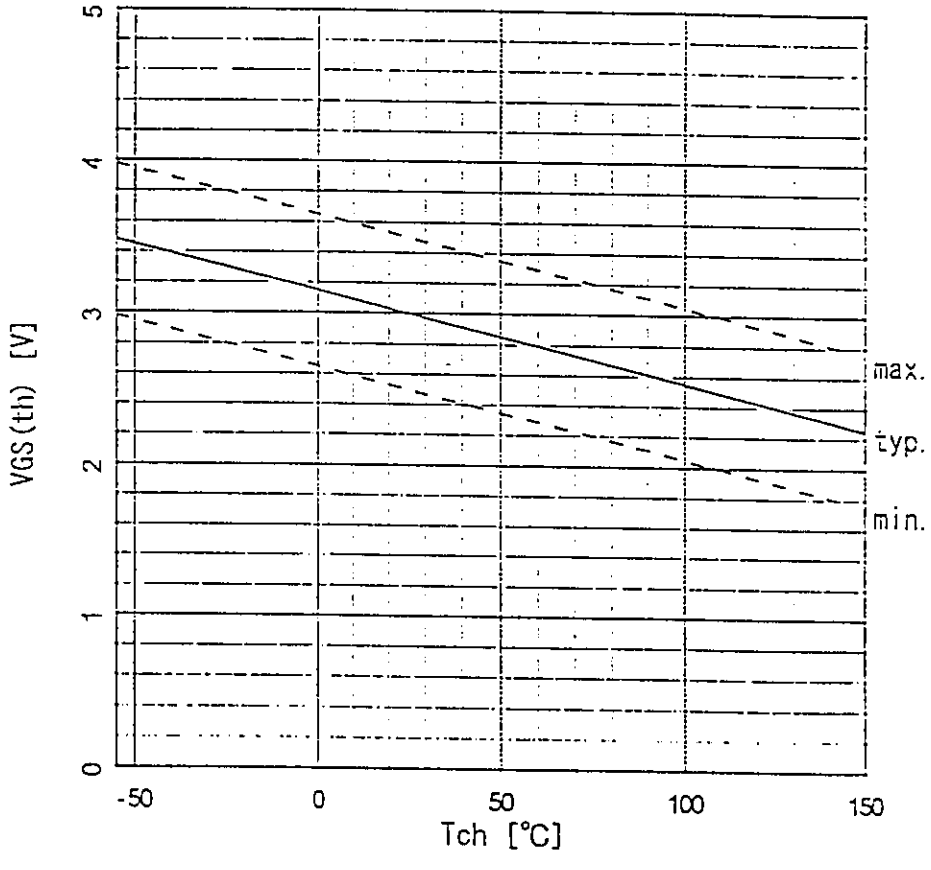
Typical drain-source on-state resistance
RDS(on)=f(ID):Tch=25℃



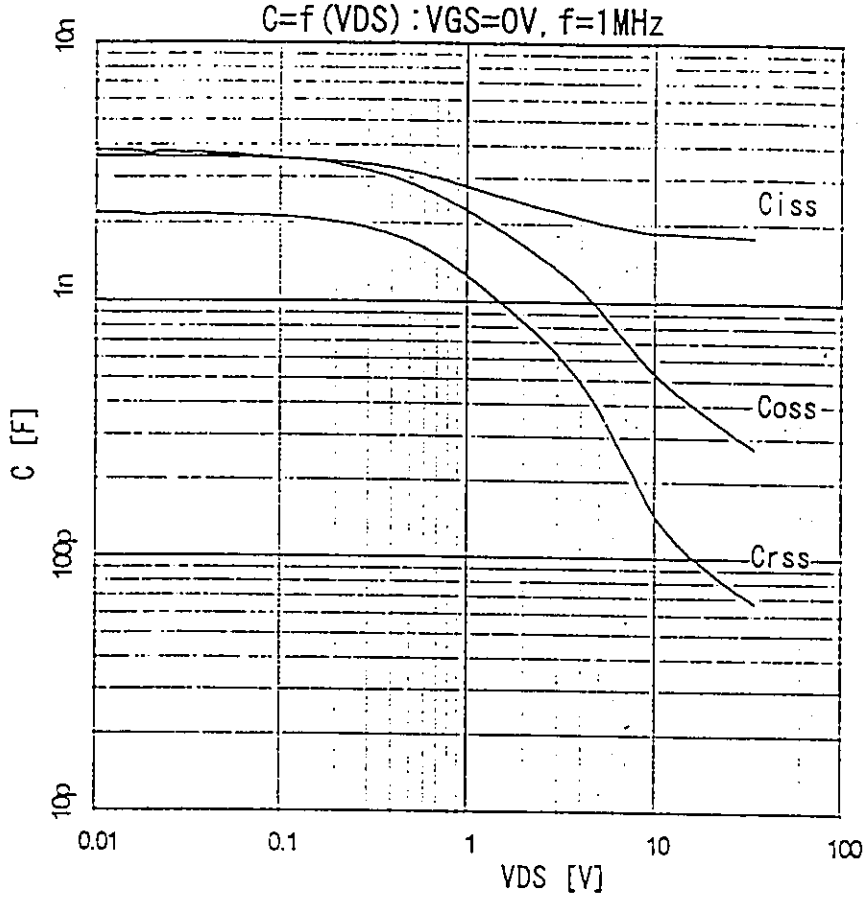
Drain-source on-state resistance
RDS(on)=f(Tch) : ID=10A, VGS=10V



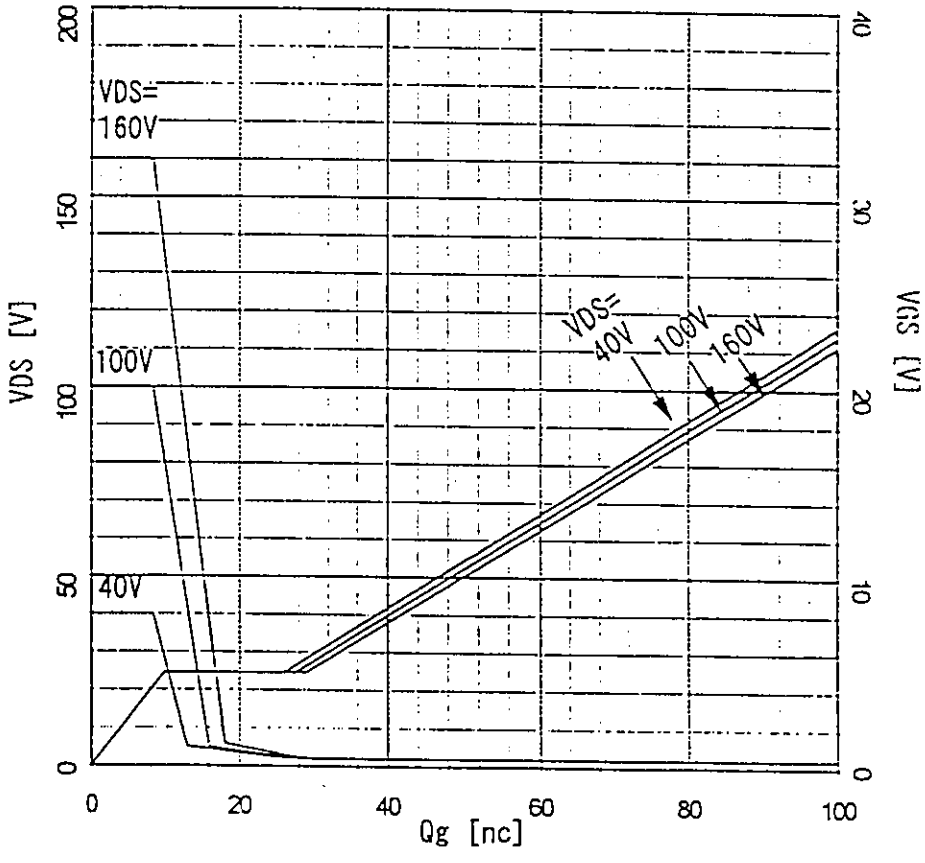
Gate threshold voltage
VGS(th)=f(Tch) : ID=1mA, VDS=VGS



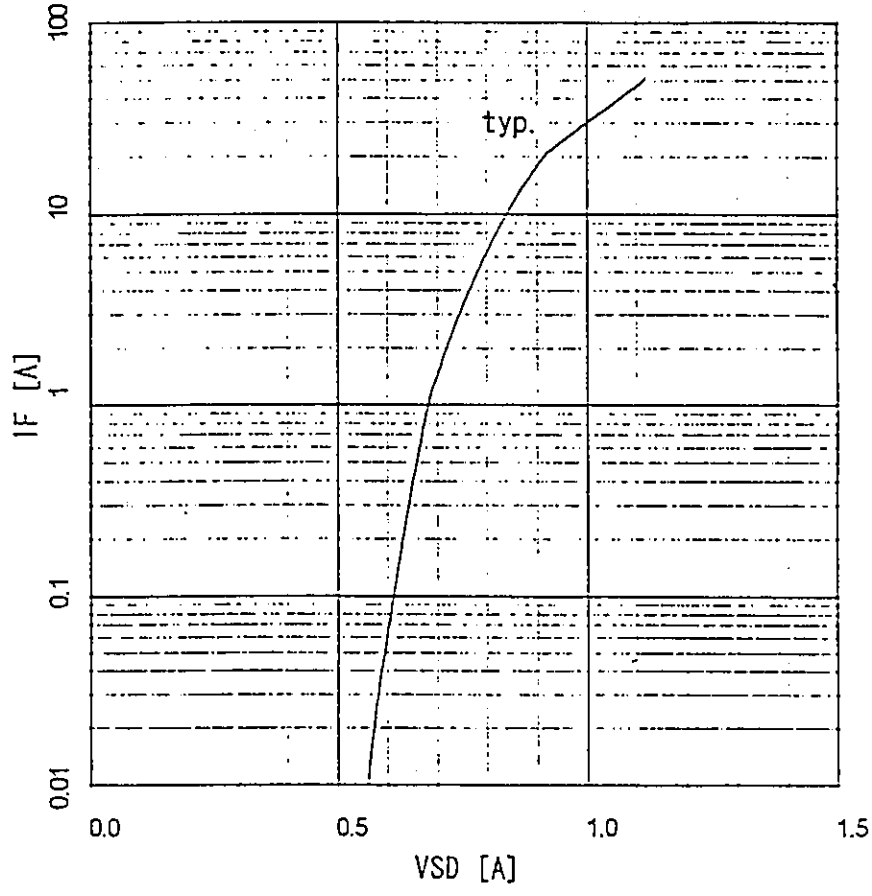
Typical capacitances
C=f(VDS):VGS=0V, f=1MHz



Typical gate charge characteristices
VGS=f(Qg):ID=20A



Forward characteristic of reverse diode
IF=f(VSD):80μs pules test



Transient thermal impedance
Zthch=f(t) parameter:D=t/T